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Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

**PEMB4; PUMB4** PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

Product data sheet Supersedes data of 2001 Sep 14

2003 Oct 15



# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMB4; PUMB4

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	_	_
TR2	PNP	_	-	-
R1	bias resistor	10	_	kΩ
R2	bias resistor	open	_	_

**QUICK REFERENCE DATA** 

#### **DESCRIPTION**

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACE	KAGE	MARKING CODE	NPN/PNP	NPN/NPN
TTPE NOWIBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMB4	SOT666	-	B4	PEMD4	PEMH4
PUMB4	SOT363	SC-88	B*4 <sup>(1)</sup>	PUMD4	PUMH4

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING
ITPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION
PEMB4	6 5 4	1	emitter TR1
PUMB4		2	base TR1
		3	collector TR2
		4	emitter TR2
		5	base TR2
	R1	6	collector TR1
	Top view MAM452		
	•		

## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

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#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
I TPE NUMBER	NAME	DESCRIPTION	VERSION
PEMB4	_	plastic surface mounted package; 6 leads	SOT666
PUMB4	_	plastic surface mounted package; 6 leads	SOT363

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT				
Per transistor									
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V				
$V_{CEO}$	collector-emitter voltage	open base	_	-50	V				
$V_{EBO}$	emitter-base voltage	open collector	_	-5	V				
lo	output current (DC)		_	-100	mA				
I <sub>CM</sub>	peak collector current		_	-100	mA				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C							
	SOT363	note 1	_	200	mW				
	SOT666	notes 1 and 2	_	200	mW				
T <sub>stg</sub>	storage temperature		-65	+150	°C				
Tj	junction temperature		_	150	°C				
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C				
Per device	<b>)</b>								
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C							
	SOT363	note 1	_	300	mW				
	SOT666	notes 1 and 2	_	300	mW				

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

## PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

# PEMB4; PUMB4

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	-	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	200	_	_	
V <sub>CEsat</sub>	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
R1	input resistor		7	10	13	kΩ
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

2003 Oct 15

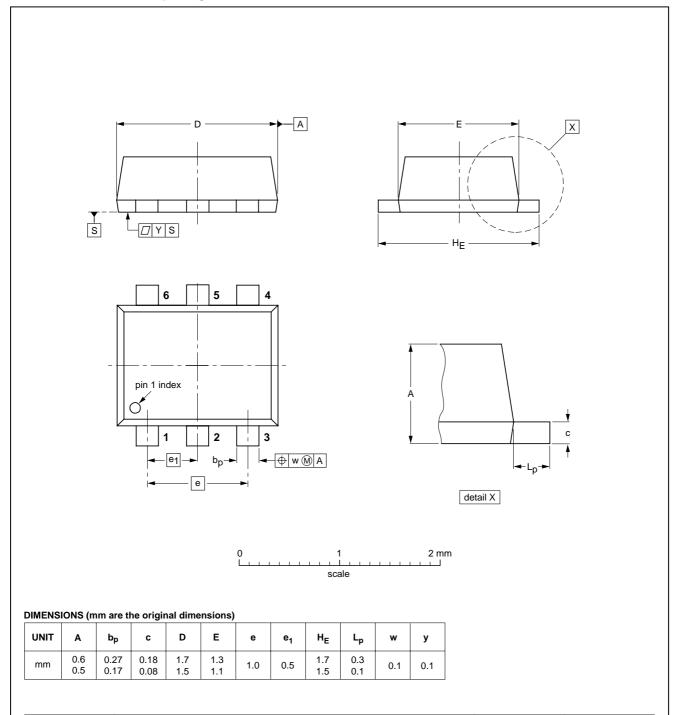
# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMB4; PUMB4

#### **PACKAGE OUTLINES**

Plastic surface mounted package; 6 leads

SOT666



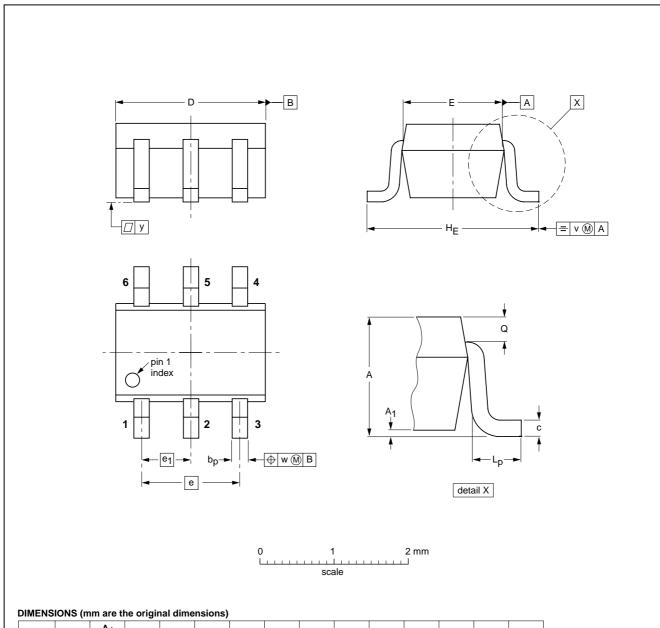
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
SOT666						<del>-01-01-04</del> 01-08-27	
	I	I			-		-

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMB4; PUMB4

#### Plastic surface mounted package; 6 leads

**SOT363** 



UNIT	A	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC JEDEC		IEC JEDEC EIAJ			PROJECTION	ISSUE DATE
SOT363			SC-88		$ \  \   \bigoplus   \big($	97-02-28	

PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

### PEMB4; PUMB4

#### **DATA SHEET STATUS**

DOCUMENT STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

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